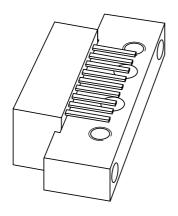
DISCRETE SEMICONDUCTORS

DATA SHEET



BGD885 860 MHz, 17 dB gain power doubler amplifier

Product specification Supersedes data of 2001 Oct 25

2001 Nov 02





860 MHz, 17 dB gain power doubler amplifier

BGD885

FEATURES

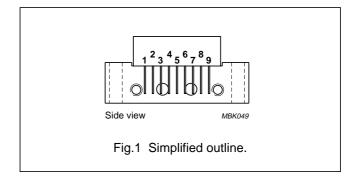
- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of 24 V (DC).

PINNING - SOT115D

PIN	DESCRIPTION	
1	input	
2, 3, 5, 6, 7	common	
4	10 V, 200 mA supply terminal	
8	+V _B	
9	output	



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	17.5	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	1	450	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V _B	DC supply voltage	_	26	V
Vi	RF input voltage	_	65	dBmV
T _{stg}	storage temperature		+100	°C
T _{mb}	operating mounting base temperature	-20	+100	°C

860 MHz, 17 dB gain power doubler amplifier

BGD885

CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; $V_B = 24 \text{ V}$; $T_{mb} = 35 \,^{\circ}\text{C}$; $Z_S = Z_L = 75 \,^{\circ}\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Gp	power gain	f = 50 MHz	16.5	17.5	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.6	dB
FL	flatness of frequency response	f = 40 to 860 MHz	_	±0.5	dB
S ₁₁	input return losses	f = 40 MHz; note 1	20	_	dB
		f = 800 to 860 MHz	10	_	dB
S ₂₂	output return losses	f = 40 MHz; note 1	20	_	dB
		f = 800 to 860 MHz	10	_	dB
d ₂	second order distortion	note 2	_	-53	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$; note 3	64	_	dBmV
		$d_{im} = -60 \text{ dB}$; note 4	63	_	dBmV
F	noise figure	f = 50 MHz	_	8	dB
		f = 550 MHz	_	8	dB
		f = 650 MHz	_	8	dB
		f = 750 MHz	_	8	dB
		f = 860 MHz	_	8	dB
I _{tot}	total current consumption (DC)	note 5	_	450	mA

Notes

- 1. Decrease per octave of 1.5 dB.
- 2. $V_p = 59 \text{ dBmV at } f_p = 349.25 \text{ MHz};$ $V_q = 59 \text{ dBmV at } f_q = 403.25 \text{ MHz};$ measured at $f_p + f_q = 752.5 \text{ MHz}.$
- 3. Measured according to DIN45004B:

```
f_p = 341.25 \text{ MHz}; V_p = V_o;
```

$$f_q = 348.25 \text{ MHz}; V_q = V_o - 6 \text{ dB};$$

$$f_r = 350.25 \text{ MHz}; V_r = V_o - 6 \text{ dB};$$

measured at $f_p + f_q - f_r = 339.25$ MHz.

4. Measured according to DIN45004B:

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f_p = 851.25 \text{ MHz}; V_p = V_o;
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$$f_q = 858.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$$

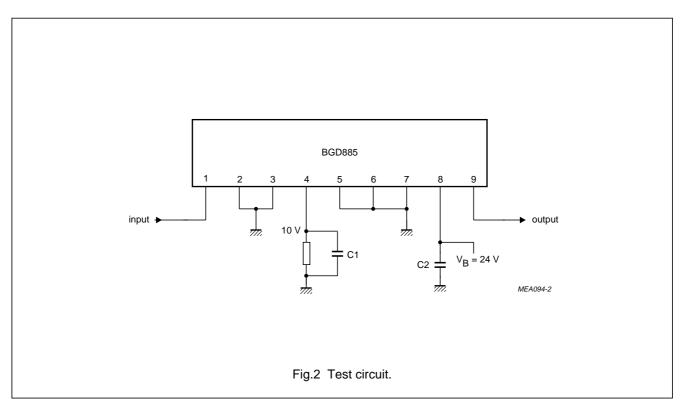
$$f_r = 860.25 \text{ MHz}; V_r = V_o - 6 \text{ dB};$$

measured at $f_p + f_q - f_r = 849.25$ MHz.

5. The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

860 MHz, 17 dB gain power doubler amplifier

BGD885



List of components (see Fig.2)

COMPONENT	DESCRIPTION	VALUE
C1	ceramic multilayer capacitor	1 nF (max.)
C2	ceramic multilayer capacitor	1 nF
R	resistor	56 Ω, 2 W

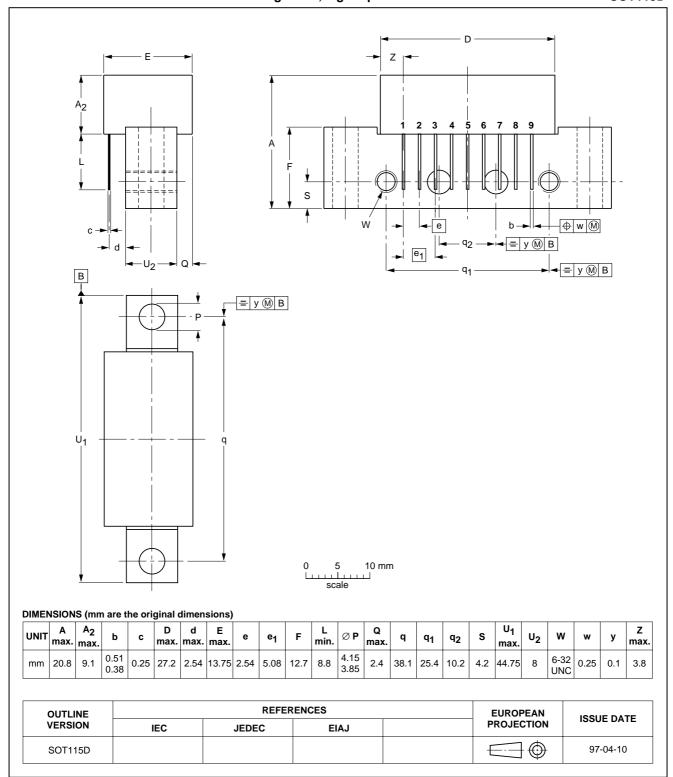
860 MHz, 17 dB gain power doubler amplifier

BGD885

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 9 gold-plated in-line leads

SOT115D



2001 Nov 02 5

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